



DMG2302UK

Product Summary

V _{(BR)DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
	90mΩ @ V _{GS} = 4.5V	2.8A
20V	120mΩ @ V _{GS} = 2.5V	2.4A

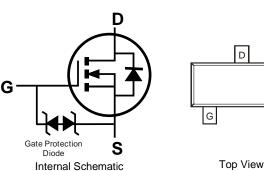
Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- **Power Management Functions**
- **DC-DC Converters**
- Motor Control

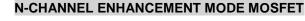
ESD protected Gate





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Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- **ESD Protected Gate**
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. • UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (93)
- Terminals Connections: See Diagram Below
- Weight: 0.009 grams (Approximate)

Ordering Information (Note 4)

Part Number	Case	Packaging
DMG2302UK-7	SOT23	3,000/Tape & Reel
DMG2302UK-13	SOT23	10,000/Tape & Reel

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

Notes:

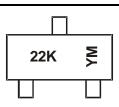
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"

and Lead-free 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and

<1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



22K = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: C = 2015) M = Month (ex: 9 = September)

Date Code Kev

Date Coactio												
Year	2015		2016	2017		2018	2019		2020	2021		2022
Code	С		D	E		F	G		Н			J
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	Ν	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Drain-Source Voltage	V _{DSS}	20	V		
Gate-Source Voltage	V _{GSS}	±12	V		
Continuous Drain Current (Note 6) V_{GS} = 4.5V	Steady State	T _A = +25°C T _A = +70°C	ID	2.8 2.2	А
Maximum Continuous Body Diode Forward Curre	ent (Note 6)	Is	1.1	А	
Pulsed Drain Current (10µs Pulse, Duty Cycle =	1%)	I _{DM}	12	А	

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)		PD	0.66	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{0JA}	192	°C/W
Total Power Dissipation (Note 6)		PD	1.1	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{0JA}	115	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

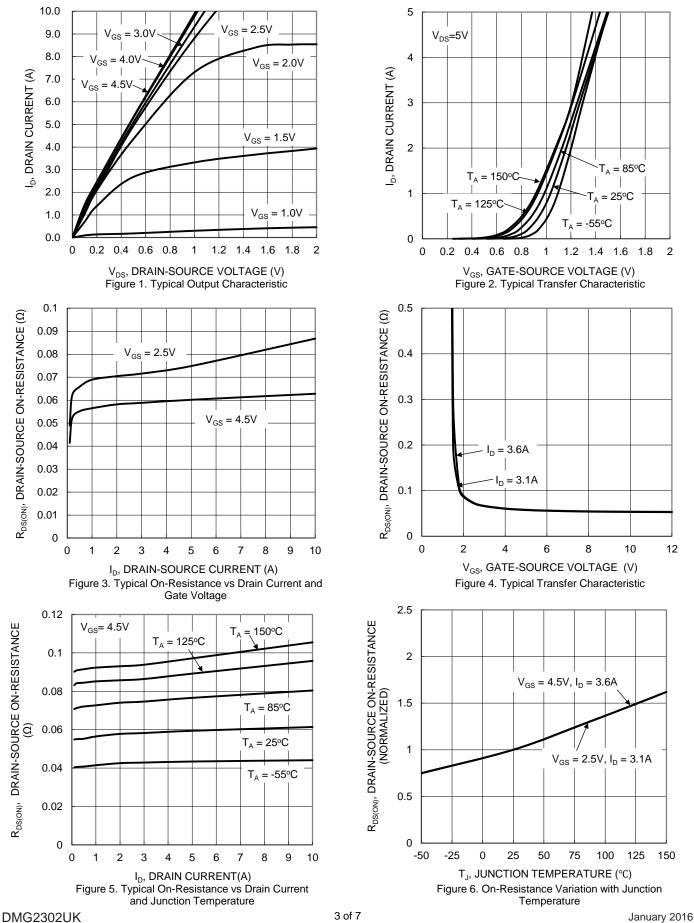
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						·
Drain-Source Breakdown Voltage	BV _{DSS}	20	—		V	$V_{GS} = 0V, I_D = 250 \mu A$
Zero Gate Voltage Drain Current $T_J = +25^{\circ}C$	I _{DSS}	—	—	10	μA	$V_{DS} = 16V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	—	—	±10	μA	$V_{GS} = \pm 10V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	0.3	0.6	1.0	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$
Static Drain-Source On-Resistance			61	90	mΩ	V _{GS} = 4.5V, I _D = 3.6A
	R _{DS(ON)}	_	80	120	11122	V _{GS} = 2.5V, I _D = 3.1A
Diode Forward Voltage	V _{SD}	_	0.7	1.2	V	$V_{GS} = 0V, I_{S} = 1.0A$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	CISS	—	130		pF	
Output Capacitance	C _{OSS}	—	26	—	pF	$V_{DS} = 10V, V_{GS} = 0V$ - f = 1.0MHz
Reverse Transfer Capacitance	C _{RSS}	—	18	_	pF	
Gate Resistance	R _G	—	2.7	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$
Total Gate Charge (V _{GS} = 4.5V)	Q _G	_	1.4	_	nC	
Total Gate Charge (V _{GS} = 10V)	Q _G	_	2.8		nC	V 40V 1 2 CA
Gate-Source Charge	Q _{GS}	_	0.1	_	nC	$V_{DS} = 10V, I_D = 3.6A$
Gate-Drain Charge	Q _{GD}	_	0.5		nC	7
Turn-On Delay Time	t _{D(ON)}	_	0.6	_	ns	
Turn-On Rise Time	t _R	—	2.7	—	ns	$V_{DS} = 10V, V_{GS} = 4.5V,$
Turn-Off Delay Time	t _{D(OFF)}	_	4.2	—	ns	$R_G = 1\Omega, R_L = 2.78\Omega$
Turn-Off Fall Time	tF	_	1.7		ns	7
Reverse Recovery Time	t _{RR}	_	5.3		ns	I _F = 3.6A, di/dt = 100A/µs
Reverse Recovery Charge	Q _{RR}	_	0.5	—	nC	I _F = 3.6A, di/dt = 100A/µs

Notes:

Device mounted on FR-4 PCB, with minimum recommended pad layout.
Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing.

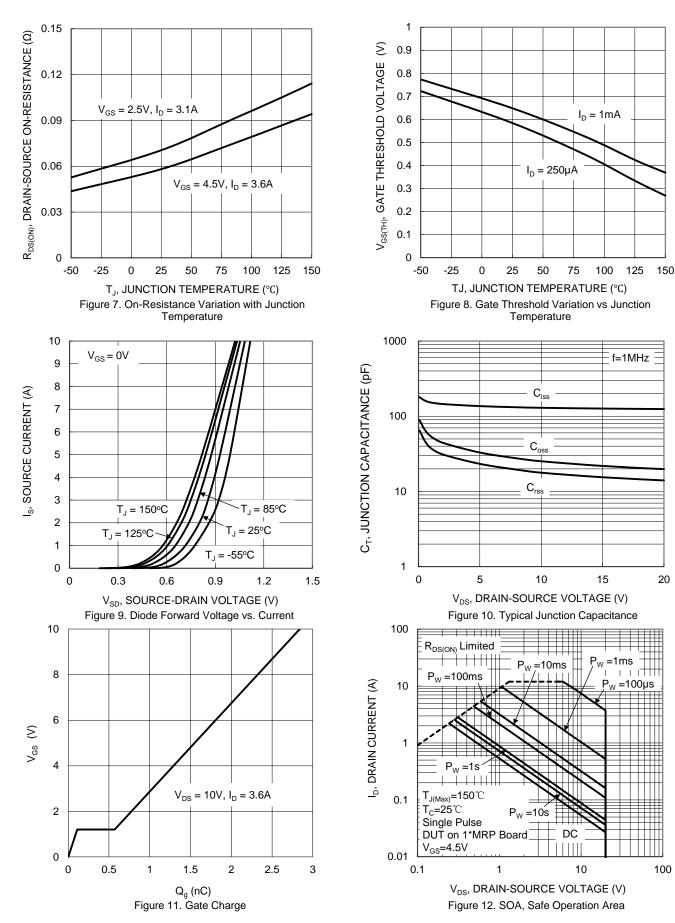




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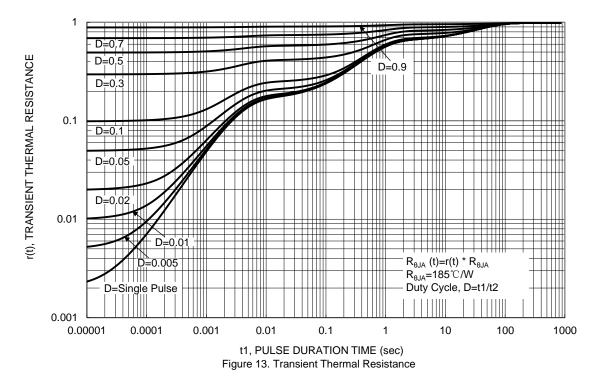
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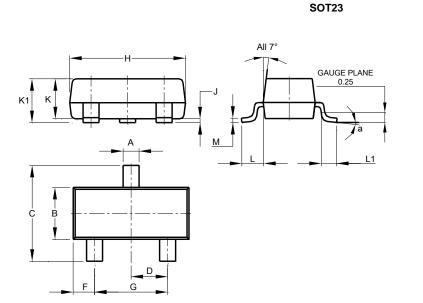






Package Outline Dimensions

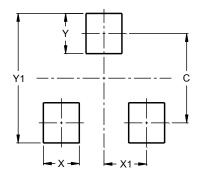
Please see AP02001 at http://www.diodes.com/_files/datasheets/ap02001.pdf for the latest version.



	SOT23								
Dim	Min	Max	Тур						
Α	0.37	0.51	0.40						
В	1.20	1.40	1.30						
С	2.30	2.50	2.40						
D	0.89	1.03	0.915						
F	0.45	0.60	0.535						
G	1.78	2.05	1.83						
н	2.80	3.00	2.90						
J	0.013	0.10	0.05						
K	0.890	1.00	0.975						
K1	0.903	1.10	1.025						
L	0.45	0.61	0.55						
L1	0.25	0.55	0.40						
М	0.085	0.150	0.110						
а	0°	8°	_						
All	All Dimensions in mm								

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/_files/datasheets/ap02001.pdf for the latest version.



SOT23

Dimensions	Value (in mm)		
С	2.0		
Х	0.8		
X1	1.35		
Y	0.9		
Y1	2.9		



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